

TPS22998 5.5-V, 10-A, 4-mΩ On-Resistance Load Switch

1 Features

- Input operating voltage range (V_{IN}): 0.2 V–5.5 V
- Bias voltage range: 2.2 V–5.5 V
- Maximum continuous current: 10 A
- ON-Resistance (R_{ON}): 4 mΩ (typ.)
- Adjustable slew rate with tri-state pin
- Quick Output Discharge (QOD): 50 Ω
- Thermal shutdown
- Low power consumption:
 - ON state (I_Q): 15 μA (typ.)
 - OFF state (I_{SD}): 3 μA (typ.)

2 Applications

- Solid state drive
- PC and notebooks
- Industrial PC
- Optical module

3 Description

The TPS22998 is a single-channel load switch that provides a configurable rise time to minimize inrush current. The device contains an N-channel MOSFET that can operate over an input voltage range of 0.2 V to 5.5 V and can support a maximum continuous current of 10 A.

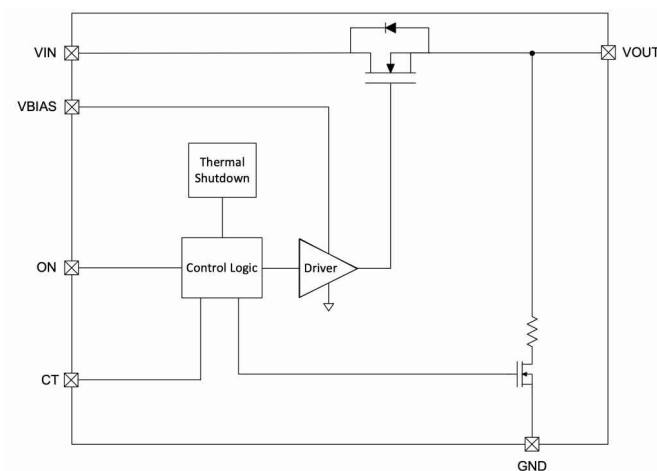
The switch is controlled by an on and off input (ON), which is capable of interfacing directly with low voltage control signals ($V_{IH} = 0.9$ V). The TPS22998 has a fixed quick output discharge when switch is turned off, pulling the output down to ground.

The TPS22998 is available in a 1.5 × 2.0 mm, 0.5 mm pitch, 10-pin WQFN package (RYZ) and is characterized for operation over the free-air temperature range of –40°C to +105°C.

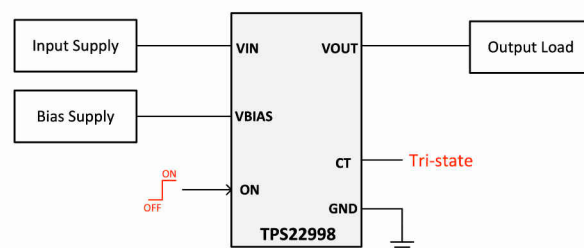
Device Information

PART NUMBER	PACKAGE ⁽¹⁾	BODY SIZE (NOM)
TPS22998	WQFN (10)	1.5 × 2.0 mm

- (1) For all available packages, see the orderable addendum at the end of the data sheet.



TPS22998 Block Diagram



TPS22998 Typical Application



Table of Contents

1 Features	1	7.2 Functional Block Diagram.....	11
2 Applications	1	7.3 Feature Description.....	11
3 Description	1	7.4 Device Functional Modes.....	12
4 Revision History	2	8 Application and Implementation	13
5 Pin Configuration and Functions	3	8.1 Application Information.....	13
6 Specifications	4	8.2 Typical Application.....	13
6.1 Absolute Maximum Ratings.....	4	9 Power Supply Recommendations	15
6.2 ESD Ratings.....	4	10 Layout	15
6.3 Recommended Operating Conditions.....	4	10.1 Layout Guidelines.....	15
6.4 Thermal Information.....	4	10.2 Layout Example.....	15
6.5 Electrical Characteristics (VBIAS = 5 V).....	5	11 Device and Documentation Support	16
6.6 Electrical Characteristics (VBIAS = 3.3 V).....	5	11.1 Receiving Notification of Documentation Updates..	16
6.7 Electrical Characteristics (VBIAS = 2.2 V).....	6	11.2 Support Resources.....	16
6.8 Switching Characteristics (VBIAS = 2.2 V to 5 V).....	7	11.3 Trademarks.....	16
6.9 Timing Diagram.....	8	11.4 Electrostatic Discharge Caution.....	16
6.10 Typical Characteristics.....	9	11.5 Glossary.....	16
7 Detailed Description	11	12 Mechanical, Packaging, and Orderable Information	17
7.1 Overview.....	11		

4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision * (October 2021) to Revision A (December 2021)	Page
• Changed data sheet status from "Advance Information" to "Production Data".....	1

5 Pin Configuration and Functions

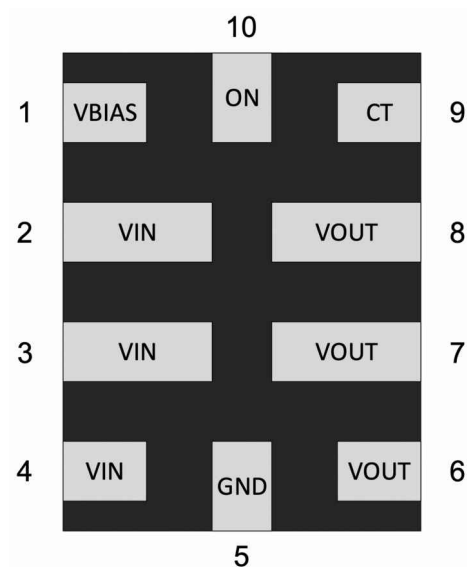


Figure 5-1. TPS22998 RYZ Package, 10-Pin WQFN (Top View)

Table 5-1. Pin Functions

PIN		I/O ⁽¹⁾	DESCRIPTION
NAME	NO.		
VBIAS	1	I	Device bias supply
VIN	2, 3, 4	I	Switch input
GND	5	G	Device ground
VOUT	6, 7, 8	O	Switch output
CT	9	I	Slew rate control – can be pulled up, left floating, or tie to ground
ON	10	I	Enable pin

(1) I = Input, O = Output, I/O = Input or Output, G = Ground, P = Power.

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V_{IN}	Input Voltage	−0.3	6	V
V_{BIAS}	Bias Voltage	−0.3	6	V
V_{ON}, V_{CT}	Control Pin Voltage	−0.3	6	V
I_{MAX}	Maximum Current		10	A
T_J	Junction temperature		Internally Limited	°C
T_{stg}	Storage temperature	−65	150	°C

- (1) Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	V
		Charged device model (CDM), per ANSI/ESDA/JEDEC JS-002 ⁽²⁾	±1000	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
 (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V_{IN}	Input Voltage	0.2		5.5	V
V_{BIAS}	Bias Voltage	2.2		5.5	V
V_{CT}	Control Pin Voltage	0		5.5	V
T_A	Ambient Temperature	−40		105	°C

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		TPS22998	UNIT
		RYZ (WQFN)	
		10 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	84.1	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	77.5	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	16.6	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	4.0	°C/W
Υ_{JB}	Junction-to-board characterization parameter	16.0	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.5 Electrical Characteristics (VBIAS = 5 V)

Over operating free-air temperature range (unless otherwise noted). Typical values are at $T_A = 25^\circ\text{C}$.

PARAMETER		TEST CONDITIONS	T _A	MIN	TYP	MAX	UNIT
Power Consumption							
I _{SD,VBIAS}	VBIAS Shutdown Current	ON = 0 V	25°C	3			uA
			–40°C to 85°C	5			uA
			–40°C to 105°C	6			uA
I _{Q,VBIAS}	VBIAS Quiescent Current	ON > V _{IH}	25°C	15			uA
			–40°C to 85°C	20			uA
			–40°C to 105°C	20			uA
I _{SD,VIN}	VIN Shutdown Current	ON = 0 V	25°C	0.1			uA
			–40°C to 85°C	1			uA
			–40°C to 105°C	2			uA
I _{ON}	ON pin leakage	ON = VBIAS	–40°C to 105°C	0.1			uA
Performance							
R _{ON}	On-Resistance	VIN = 0.2 V to 5 V	25°C	4			mΩ
			–40°C to 85°C	6			mΩ
			–40°C to 105°C	7			mΩ
V _{IH}	Turn on threshold, rising		–40°C to 105°C	0.765	0.9	1.035	V
V _{IL}	Turn off threshold, falling		–40°C to 105°C	0.595	0.7	0.805	V
V _{ON,HYST}	ON pin hysteresis		–40°C to 105°C	0.2			V
t _{ON,DEGLITCH}	On pin deglitch time		–40°C to 105°C	2	5	7	us
R _{QOD}	QOD Resistance	VOUT = VIN	25°C	50			Ω
			–40°C to 105°C	40	60		Ω
Protection							
TSD	Thermal Shutdown		-	130	150	180	°C
TSD _{HYS}	Thermal Shutdown Hysteresis		-	20			°C

6.6 Electrical Characteristics (VBIAS = 3.3 V)

Over operating free-air temperature range (unless otherwise noted). Typical values are at $T_A = 25^\circ\text{C}$.

PARAMETER		TEST CONDITIONS	T_A	MIN	TYP	MAX	UNIT
Power Consumption							
$I_{SD,VBIAS}$	VBIAS Shutdown Current	ON = 0 V	25°C		3		uA
			–40°C to 85°C			5	uA
			–40°C to 105°C			5	uA
$I_{Q,VBIAS}$	VBIAS Quiescent Current	ON > V_{IH}	25°C		15		uA
			–40°C to 85°C			20	uA
			–40°C to 105°C			20	uA
$I_{SD,VIN}$	VIN Shutdown Current	ON = 0 V	25°C		0.1		uA
			–40°C to 85°C			1	uA
			–40°C to 105°C			3	uA
I_{ON}	ON pin leakage	ON = VBIAS	–40°C to 105°C		0.1	1	uA
Performance							

6.6 Electrical Characteristics (VBIAS = 3.3 V) (continued)

Over operating free-air temperature range (unless otherwise noted). Typical values are at $T_A = 25^\circ\text{C}$.

PARAMETER		TEST CONDITIONS	T _A	MIN	TYP	MAX	UNIT
R _{ON}	On-Resistance	VIN = 0.2 V to 3.3 V	25°C	4			mΩ
			−40°C to 85°C	7			mΩ
			−40°C to 105°C	7			mΩ
V _{IH}	ON pin turn on threshold, rising		−40°C to 105°C	0.765	0.9	1.035	V
V _{IL}	ON pin turn off threshold, falling		−40°C to 105°C	0.595	0.7	0.805	V
V _{ON, HYST}	ON pin hysteresis		−40°C to 105°C	0.2			V
t _{ON,DEGLITCH}	On pin deglitch time		−40°C to 105°C	2	5	6.5	us
R _{QOD}	QOD Resistance	VOUT = VIN	25°C	50			Ω
			−40°C to 105°C	40	60		Ω
Protection							
TSD	Thermal Shutdown		-	130	150	180	°C
TSD _{HYS}	Thermal Shutdown Hysteresis		-	20			°C

6.7 Electrical Characteristics (VBIAS = 2.2 V)

Over operating free-air temperature range (unless otherwise noted). Typical values are at $T_A = 25^\circ\text{C}$.

PARAMETER		TEST CONDITIONS	T _A	MIN	TYP	MAX	UNIT
Power Consumption							
I _{SD,VBIAS}	VBIAS Shutdown Current	ON = 0 V	25°C	3			μA
			−40°C to 85°C	5			μA
			−40°C to 105°C	5			μA
I _{Q,VBIAS}	VBIAS Quiescent Current	ON > V _{IH}	25°C	15			μA
			−40°C to 85°C	20			μA
			−40°C to 105°C	20			μA
I _{SD,VIN}	VIN Shutdown Current	ON = 0 V	25°C	0.1			μA
			−40°C to 85°C	1			μA
			−40°C to 105°C	3			μA
I _{ON}	ON pin leakage	ON = VBIAS	−40°C to 105°C	0.1			1 μA
Performance							
R _{ON}	On-Resistance	VIN = 0.2 V to 2.2 V	25°C	4.3			mΩ
			−40°C to 85°C	7			mΩ
			−40°C to 105°C	7			mΩ
V _{IH}	ON pin turn on threshold, rising		−40°C to 105°C	0.765	0.9	1.035	V
V _{IL}	ON pin turn off threshold, falling		−40°C to 105°C	0.595	0.7	0.805	V
V _{ON, HYST}	ON pin hysteresis		−40°C to 105°C	0.2			V
t _{ON, DEGLITCH}	On pin deglitch time		−40°C to 105°C	2	4.5	6.5	μs
R _{QOD}	QOD Resistance	VOUT = VIN	25°C	50			Ω
			−40°C to 105°C	40	60		Ω
Protection							
TSD	Thermal Shutdown		-	130	150	180	°C
TSD _{HYS}	Thermal Shutdown Hysteresis		-	20			°C

6.8 Switching Characteristics (VBIAS = 2.2 V to 5 V)

Over operating free-air temperature range (unless otherwise noted), C_{IN}=47uF. Typical values are at T_A = 25°C, C_L = 0.1μF, and a current load of 1mA.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
VIN = 5 V						
t _{ON}	Turn ON time	CT = Open		250		us
t _{ON}	Turn ON time	CT = V _{BIAS}		1870		us
t _{ON}	Turn ON time	CT = GND		3728		us
t _{RISE}	Rise time	CT = Open		225		us
t _{RISE}	Rise time	CT = V _{BIAS}		1838		us
t _{RISE}	Rise time	CT = GND		3697		us
t _D	Delay time	CT = Open		26		us
t _D	Delay time	CT = V _{BIAS}		31		us
t _D	Delay time	CT = GND		31		us
t _{FALL}	Fall time	CT = Open		11		us
t _{OFF}	Turn OFF time	CT = Open		3		us
VIN = 3.3 V						
t _{ON}	Turn ON time	CT = Open		175		us
t _{ON}	Turn ON time	CT = V _{BIAS}		1261		us
t _{ON}	Turn ON time	CT = GND		3586		us
t _{RISE}	Rise time	CT = Open		150		us
t _{RISE}	Rise time	CT = V _{BIAS}		1232		us
t _{RISE}	Rise time	CT = GND		2478		us
t _D	Delay time	CT = Open		26		us
t _D	Delay time	CT = V _{BIAS}		29		us
t _D	Delay time	CT = GND		29		us
t _{FALL}	Fall time	CT = Open		11		us
t _{OFF}	Turn OFF time	CT = Open		3		us
VIN = 1.8 V						
t _{ON}	Turn ON time	CT = Open		102		us
t _{ON}	Turn ON time	CT = V _{BIAS}		664		us
t _{ON}	Turn ON time	CT = GND		1302		us
t _{RISE}	Rise time	CT = Open		75		us
t _{RISE}	Rise time	CT = V _{BIAS}		634		us
t _{RISE}	Rise time	CT = GND		1272		us
t _D	Delay time	CT = Open		27		us
t _D	Delay time	CT = V _{BIAS}		29		us
t _D	Delay time	CT = GND		30		us
t _{FALL}	Fall time	CT = Open		11		us
t _{OFF}	Turn OFF time	CT = Open		3		us
VIN = 0.6 V						
t _{ON}	Turn ON time	CT = Open		51		us
t _{ON}	Turn ON time	CT = V _{BIAS}		213		us
t _{ON}	Turn ON time	CT = GND		393		us
t _{RISE}	Rise time	CT = Open		23		us
t _{RISE}	Rise time	CT = V _{BIAS}		183		us
t _{RISE}	Rise time	CT = GND		365		us

6.8 Switching Characteristics (VBIAS = 2.2 V to 5 V) (continued)

Over operating free-air temperature range (unless otherwise noted), $C_{IN}=47\mu F$. Typical values are at $T_A = 25^\circ C$, $C_L = 0.1\mu F$, and a current load of 1mA.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_D	Delay time	CT = Open		27		us
t_D	Delay time	CT = V_{BIAS}		29		us
t_D	Delay time	CT = GND		29		us
t_{FALL}	Fall time	CT = Open		10		us
t_{OFF}	Turn OFF time	CT = Open		4		us
VIN = 0.285 V						
t_{ON}	Turn ON time	CT = Open		37		us
t_{ON}	Turn ON time	CT = V_{BIAS}		96		us
t_{ON}	Turn ON time	CT = GND		158		us
t_{RISE}	Rise time	CT = Open		11		us
t_{RISE}	Rise time	CT = V_{BIAS}		66		us
t_{RISE}	Rise time	CT = GND		128		us
t_D	Delay time	CT = Open		27		us
t_D	Delay time	CT = V_{BIAS}		29		us
t_D	Delay time	CT = GND		30		us
t_{FALL}	Fall time	CT = Open		9		us
t_{OFF}	Turn OFF time	CT = Open		4		us

6.9 Timing Diagram

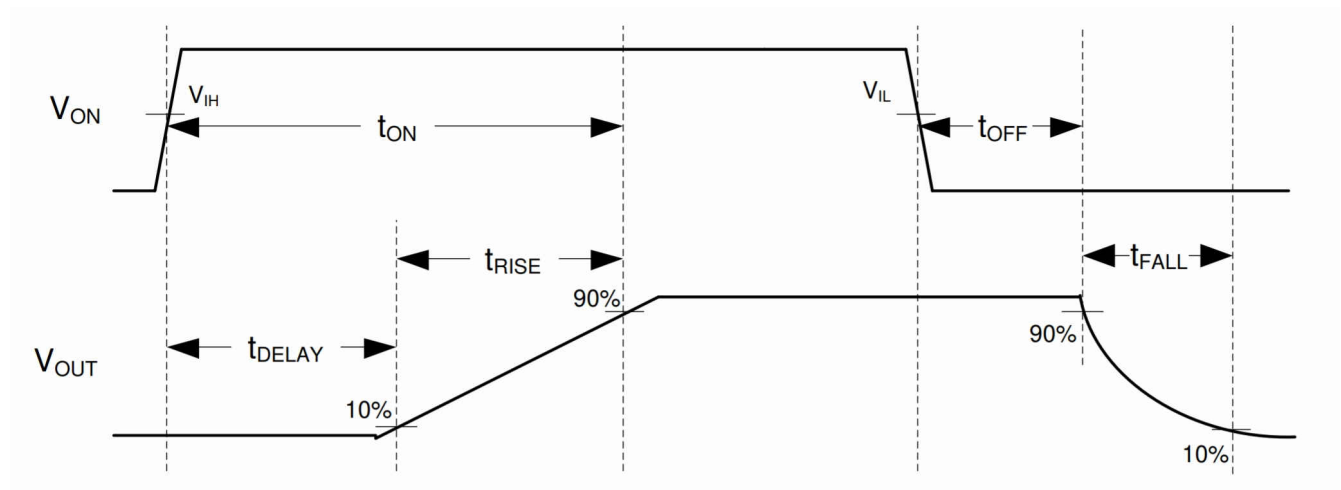


Figure 6-1. TPS22998 Timing Diagram

6.10 Typical Characteristics

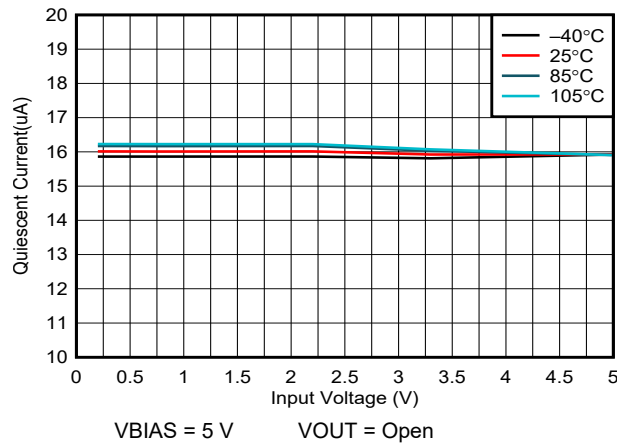


Figure 6-2. Quiescent Current vs Input Voltage

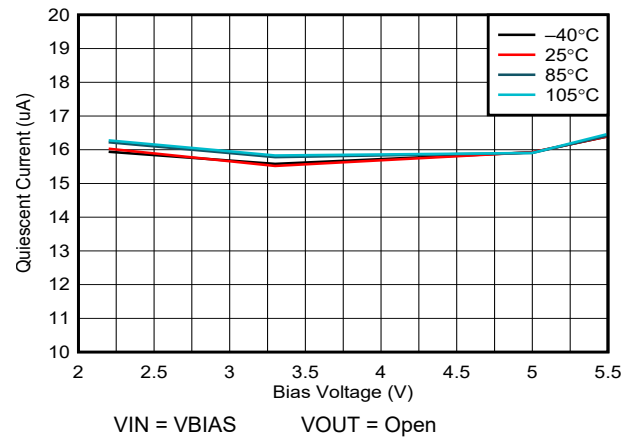


Figure 6-3. Quiescent Current vs Bias Voltage

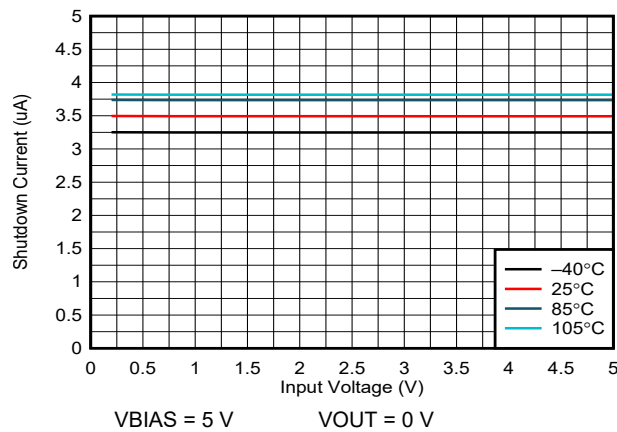


Figure 6-4. VBIAS Shutdown Current vs Input Voltage

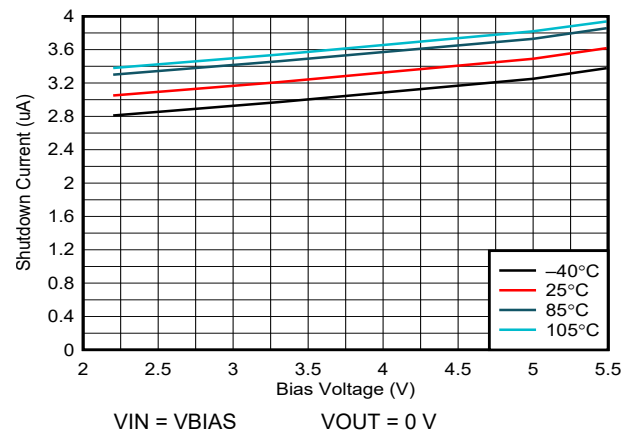


Figure 6-5. VBIAS Shutdown Current vs Bias Voltage

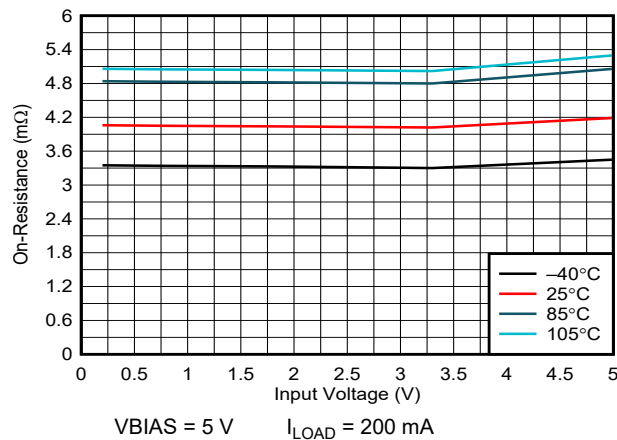


Figure 6-6. On-Resistance vs Input Voltage

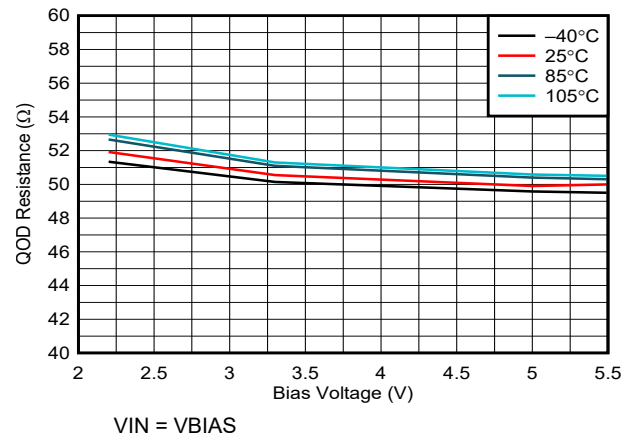
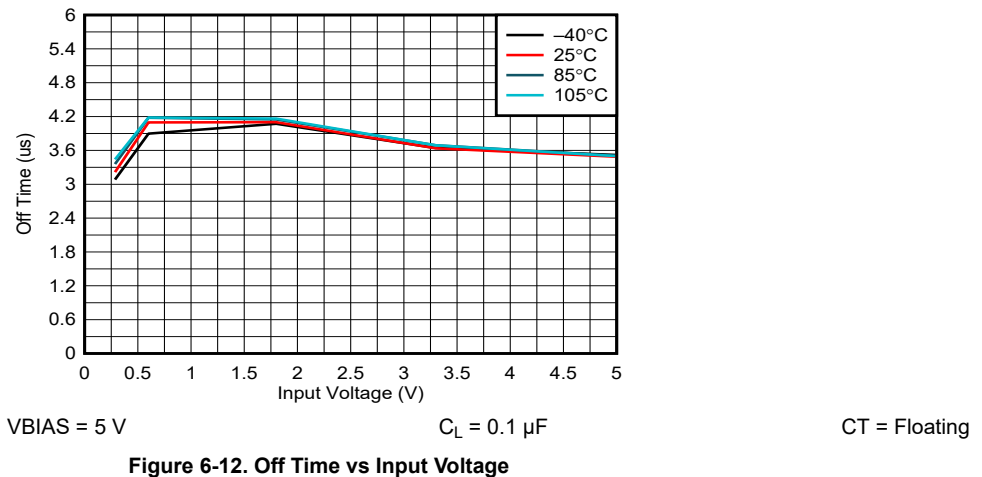
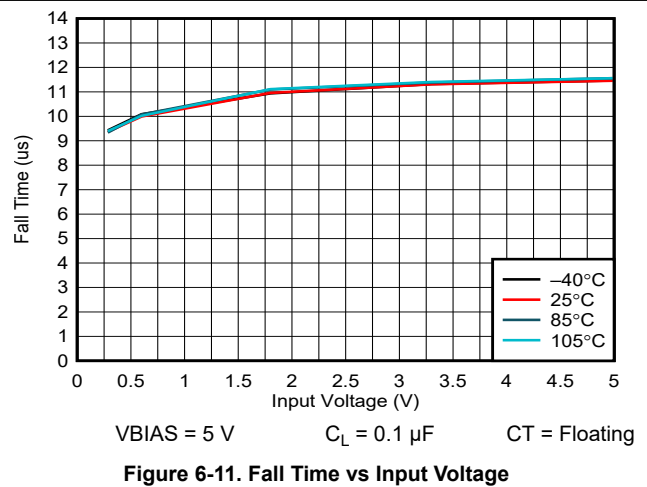
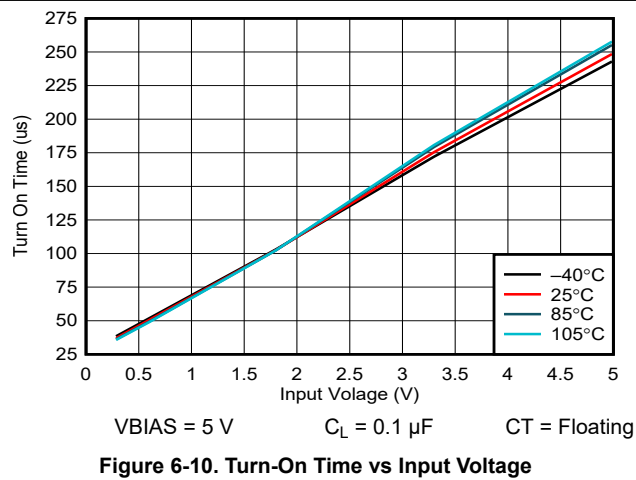
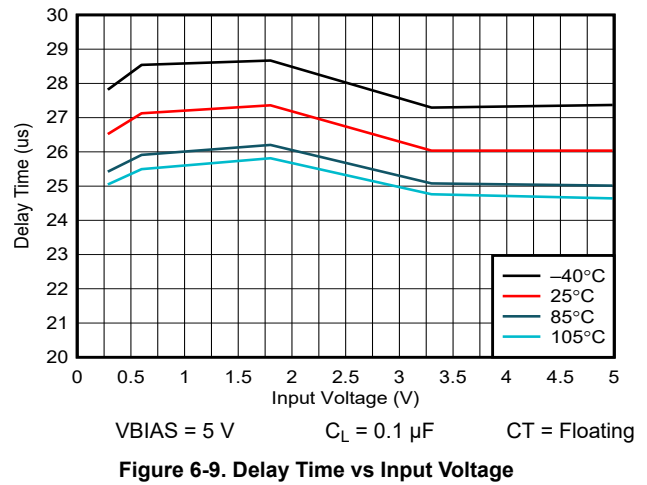
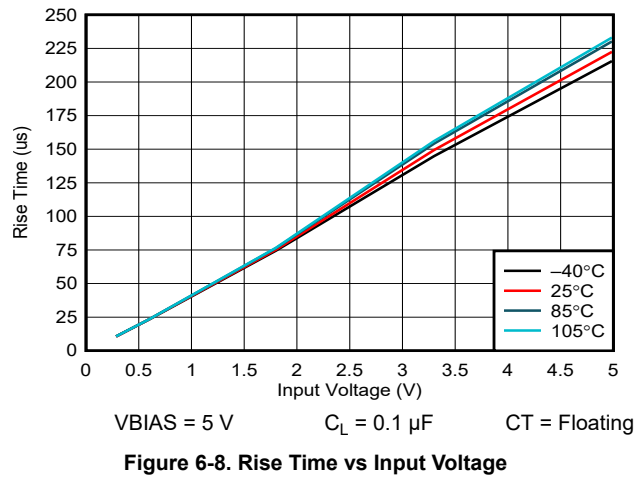


Figure 6-7. QOD Resistance vs Bias Voltage

6.10 Typical Characteristics (continued)



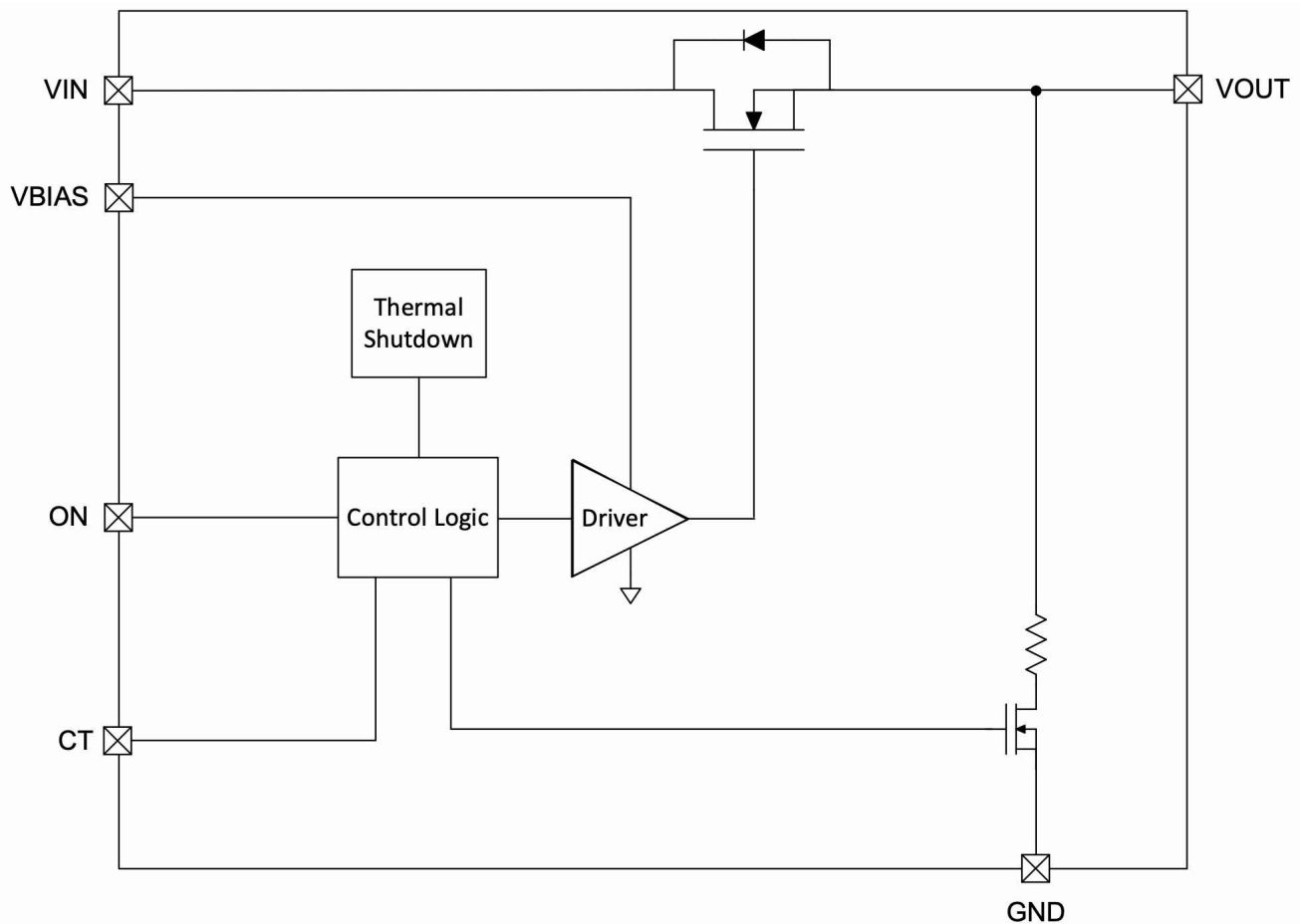
7 Detailed Description

7.1 Overview

The TPS22998 device is a single-channel load switch with a 4-m Ω power MOSFET designed to operate up to 10 A. The voltage range is 0.2 V to 5.5 V. A configurable rise time provides flexibility for power sequencing and minimizes inrush current for high capacitance loads.

An enable pin (ON) controls the switch, which is capable of interfacing directly with low voltage GPIO signals. The TPS22998 device uses quick output discharge when switch turns off, pulling the output down to 0 V through an internal 50- Ω resistor.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 ON and OFF Control

The ON pin controls the state of the switch. The ON pin is compatible with standard GPIO logic threshold so it can be used in a wide variety of applications. When the pin pull high, the device enables, and when it is low, the device disables.

7.3.2 Adjustable Slew Rate

The CT pin is a tri-state pin, meaning that it has three different slew rates depending on the connection to the pin. The CT pin can be grounded, pulled high, or left floating. Floating defines as an effective resistance to GND or other pins greater than 10 M Ω .

7.3.3 Thermal Shutdown

When the device temperature reaches 150°C (typical), the device shuts itself off to prevent thermal damage. After it cools off by about 20°C, the device turns back on. If the device is kept in a thermally stressful environment, then the device oscillates between these two states until it can keep its temperature below the thermal shutdown point.

7.4 Device Functional Modes

The below table summarizes the device functional modes:

ON	Fault Condition	VOUT State
L	None	QOD to GND
H	None	Connected to VIN
H	Thermal shutdown	QOD to GND

8 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application Information

This section highlights some of the design considerations when implementing this device in various applications.

8.2 Typical Application

This typical application demonstrates how to use the TPS22998 device to limit startup inrush current.

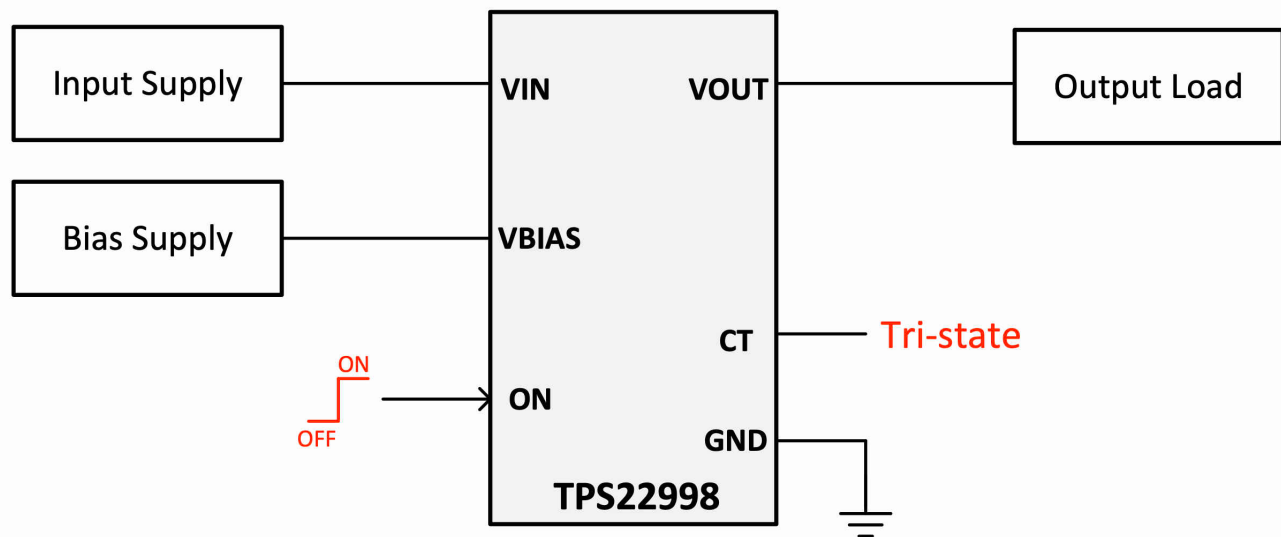


Figure 8-1. TPS22998 Basic Application

8.2.1 Design Requirements

For this example, the values below are used as the design parameters.

Table 8-1. Design Parameters

PARAMETER	VALUE
V_{BIAS}	3.3 V
V_{IN}	1.8 V
Load capacitance	470 μ F
Maximum inrush current	1 A

8.2.2 Detailed Design Procedure

When the switch enables, the charge up the output capacitance from 0 V to the set value (1.8 V in this example). This charge arrives in the form of inrush current. Calculate inrush current using [Equation 1](#).

$$\text{Inrush Current} = C_L \times dV_{OUT}/dt \quad (1)$$

Where:

- C_L is the output capacitance.
- dV_{OUT} is the change in V_{OUT} during the ramp up of the output voltage when device is enabled. Because rise time is 10% of V_{OUT} to 90% of V_{OUT} , this is 80% of the V_{IN} value.
- dt is the rise time in V_{OUT} during the ramp up of the output voltage when the device is enabled.

The TPS22998 offers an adjustable rise time for V_{OUT} , allowing the user to control the inrush current during turn on. Calculate the appropriate rise time using the design requirements and the inrush current equation as shown below.

$$1A = 470 \mu F \times (1.8 V \times 80\%) / dt \quad (2)$$

$$dt = 677 \mu s \quad (3)$$

To ensure an inrush current of less than 1 A, a C_T setting that yields a rise time of more than 677 μs must be chosen. By pulling the CT pin high, a rise time of 900 μs is selected, limiting the inrush current to below 1 A.

8.2.3 Application Performance Plots

The below scope shot shows the TPS22998 turning on into a 470- μF load with the CT pin tied to V_{BIAS} .

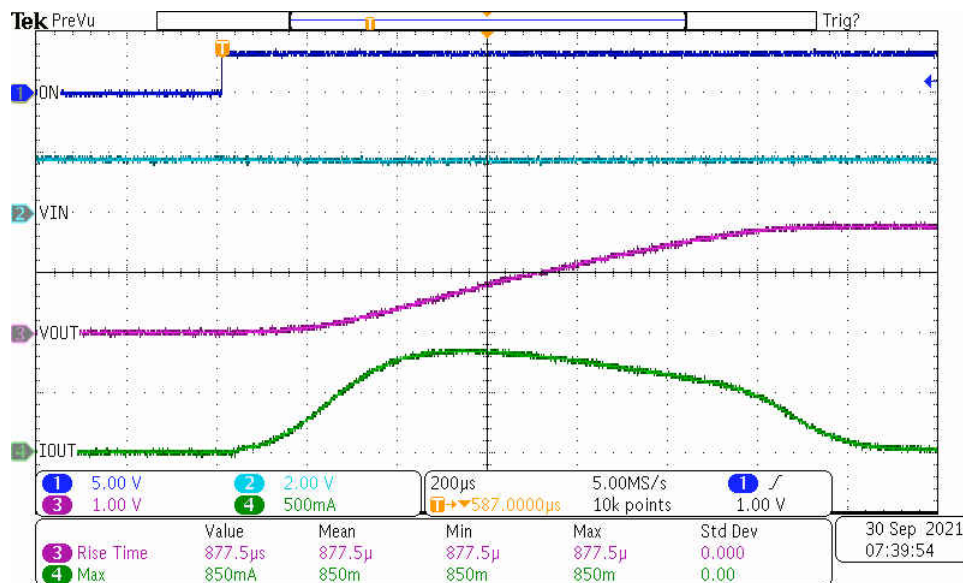


Figure 8-2. TPS22998 Turn-On into 470 μF ($CT = V_{BIAS}$)

9 Power Supply Recommendations

The TPS22998 device is designed to operate with a VIN range of 0.2 V to 5.5 V. Regulate the VIN power supply well and place as close to the device terminal as possible. The power supply must be able to withstand all transient load current steps. In most situations, using an input capacitance (C_{IN}) of 1 μ F is sufficient to prevent the supply voltage from dipping when the switch is turned on. In cases where the power supply is slow to respond to a large transient current or large load current step, additional bulk capacitance can be required on the input.

10 Layout

10.1 Layout Guidelines

For best performance, all traces must be as short as possible. To be most effective, place the input and output capacitors close to the device terminal as possible. Using wide traces for VIN, VOUT, and GND helps minimize the parasitic electrical effects.

10.2 Layout Example

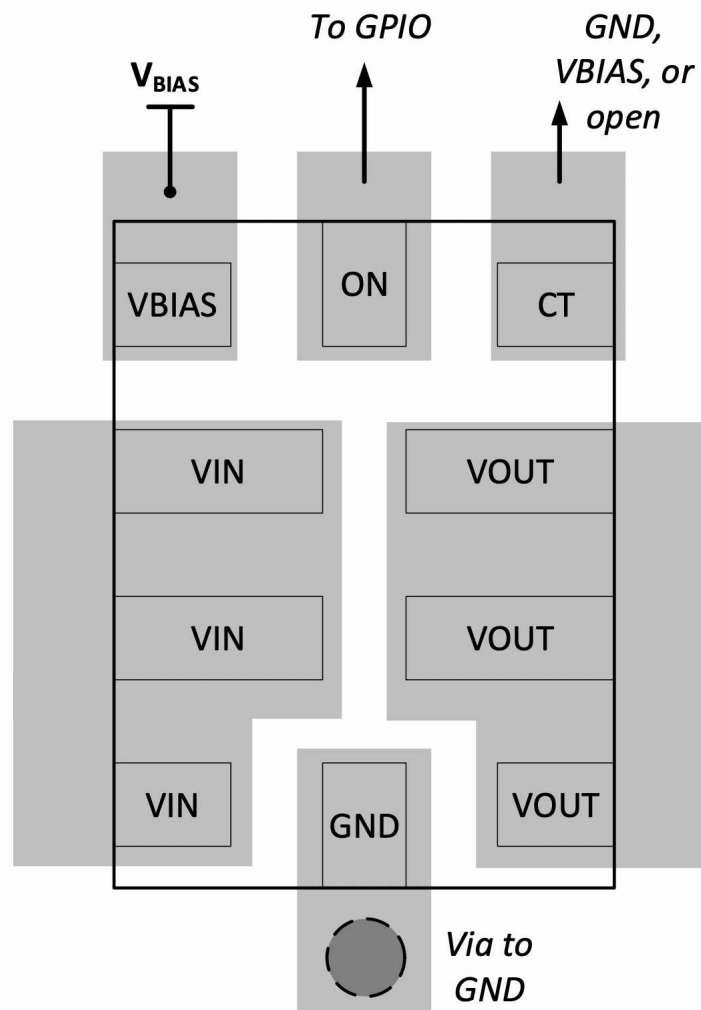


Figure 10-1. TPS22998 Layout Example

11 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

11.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

11.2 Support Resources

[TI E2E™ support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

11.3 Trademarks

TI E2E™ is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

11.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

11.5 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
TPS22998RYZR	Active	Production	WQFN-HR (RYZ) 10	3000 LARGE T&R	Yes	SN	Level-2-260C-1 YEAR	-40 to 105	1LF
TPS22998RYZR.A	Active	Production	WQFN-HR (RYZ) 10	3000 LARGE T&R	Yes	SN	Level-2-260C-1 YEAR	-40 to 105	1LF

- ⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).
- ⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.
- ⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.
- ⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.
- ⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.
- ⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "-" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer:The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS22998RYZR	WQFN-HR	RYZ	10	3000	180.0	8.4	1.75	2.25	1.0	4.0	8.0	Q1

TAPE AND REEL BOX DIMENSIONS



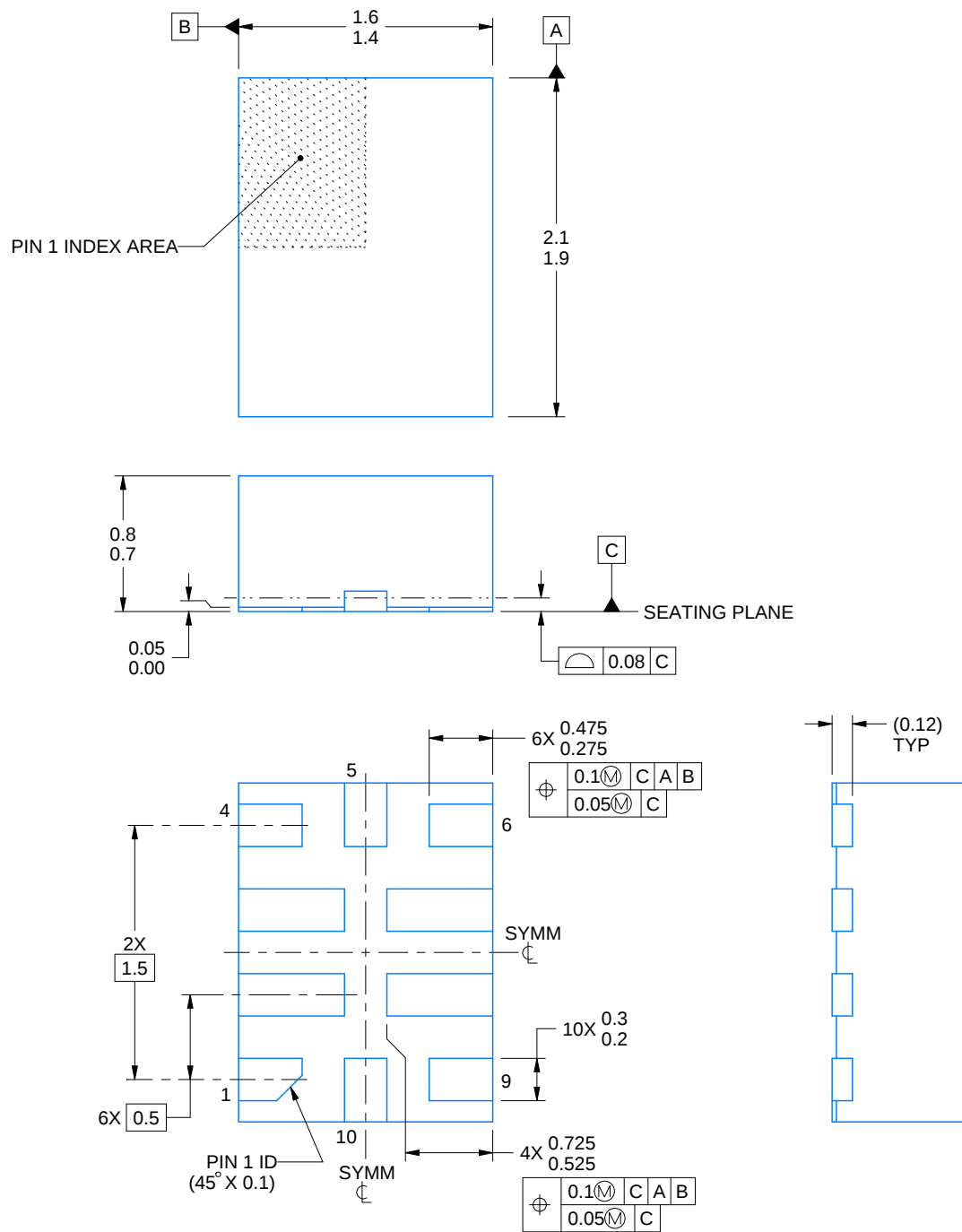
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS22998RYZR	WQFN-HR	RYZ	10	3000	210.0	185.0	35.0



WQFN-HR - 0.8 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



4226834/B 06/2021

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

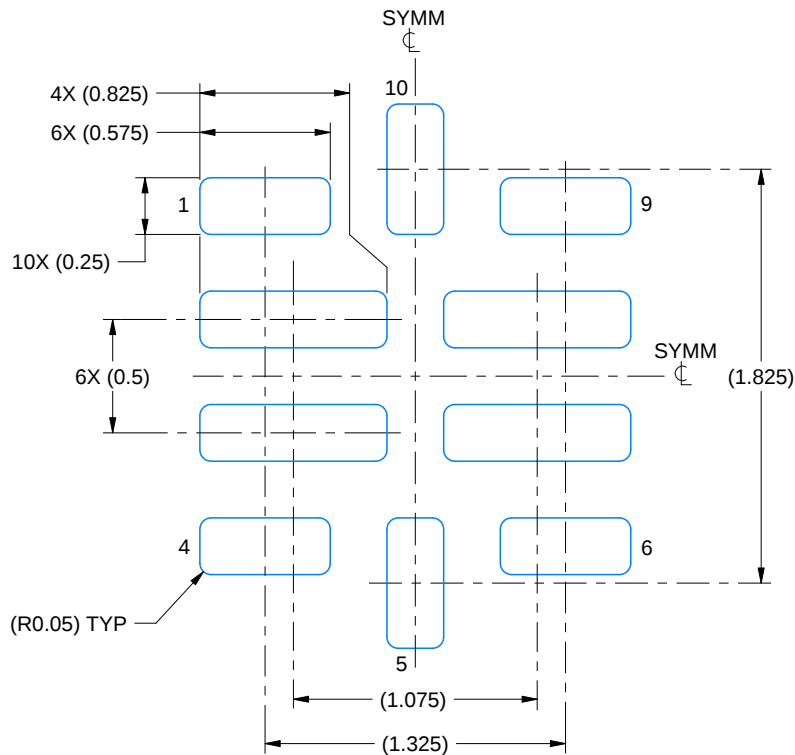
2. This drawing is subject to change without notice.

EXAMPLE BOARD LAYOUT

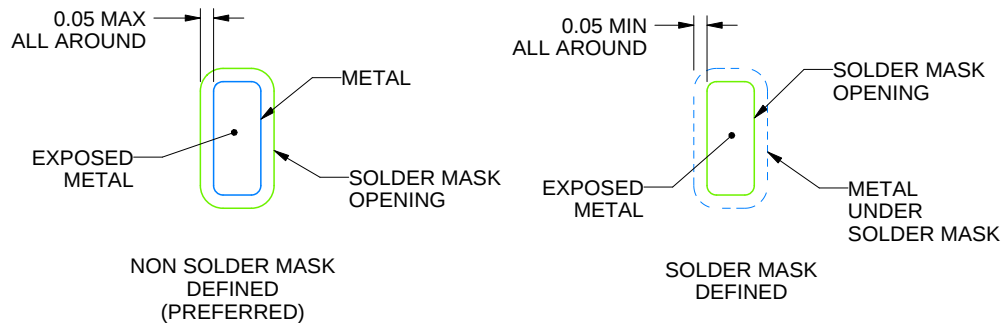
RYZ0010A

WQFN-HR - 0.8 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:30X



SOLDER MASK DETAILS
NOT TO SCALE

4226834/B 06/2021

NOTES: (continued)

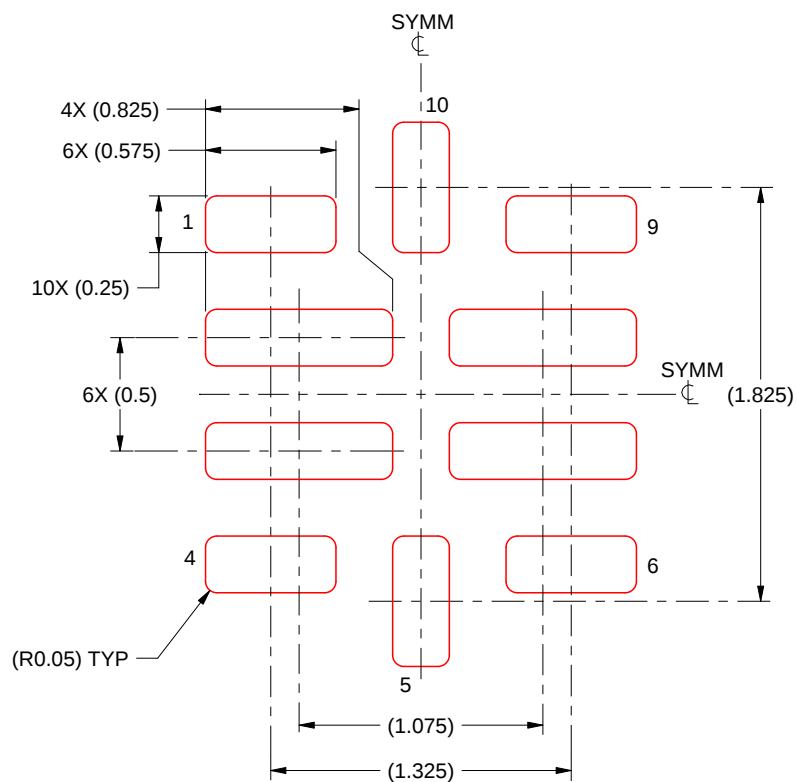
3. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/sluea271).

EXAMPLE STENCIL DESIGN

RYZ0010A

WQFN-HR - 0.8 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



SOLDER PASTE EXAMPLE
BASED ON 0.1 mm THICKNESS
SCALE: 30X

4226834/B 06/2021

NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATA SHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to [TI's Terms of Sale](#) or other applicable terms available either on [ti.com](https://www.ti.com) or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

TI objects to and rejects any additional or different terms you may have proposed.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265
Copyright © 2025, Texas Instruments Incorporated